
2SD2101

Silicon NPN Triple Diffused

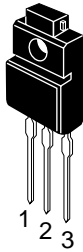
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Application

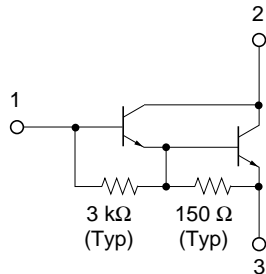
Low frequency power amplifier

Outline

TO-220FM



- 1. Base
- 2. Collector
- 3. Emitter



Absolute Maximum Ratings (Ta = 25°C)

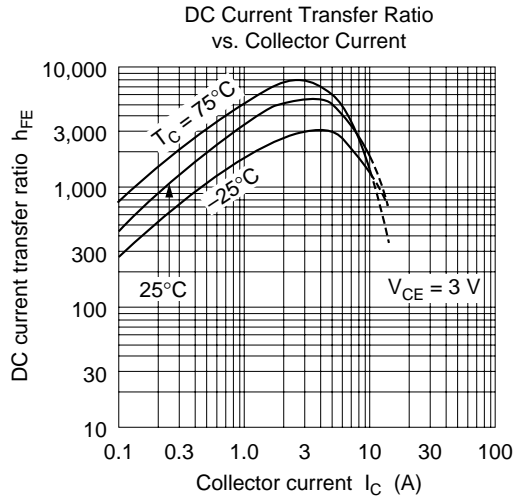
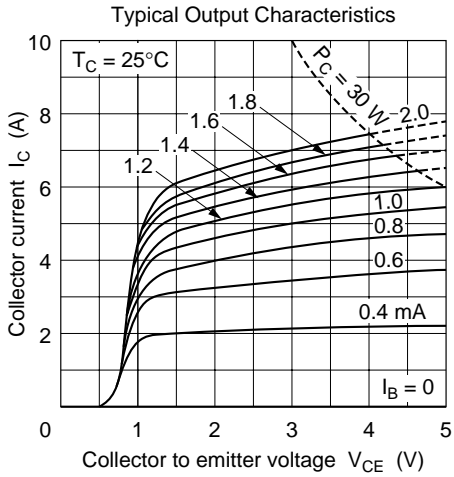
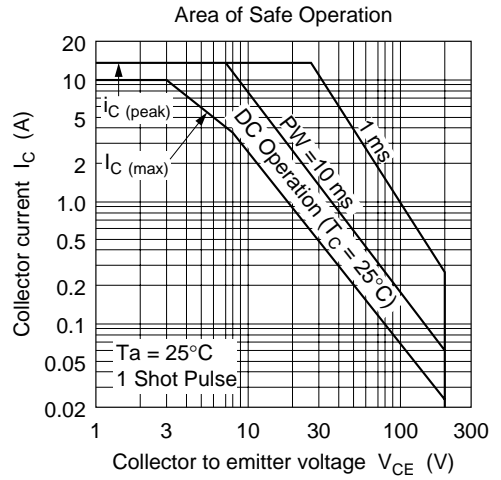
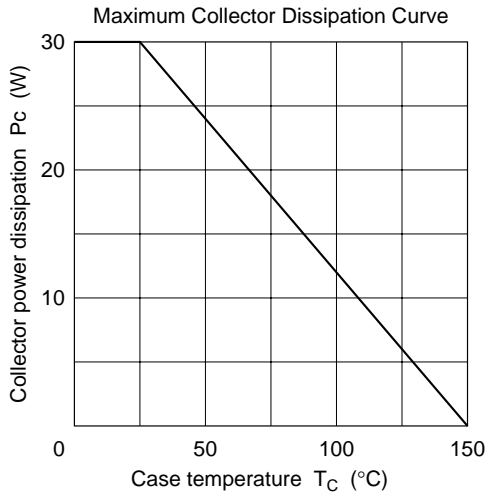
Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	200	V
Collector to emitter voltage	V_{CEO}	200	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	10	A
Collector peak current	$I_{C(peak)}$	15	A
Collector power dissipation	P_C	2	W
	P_C^{*1}	30	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

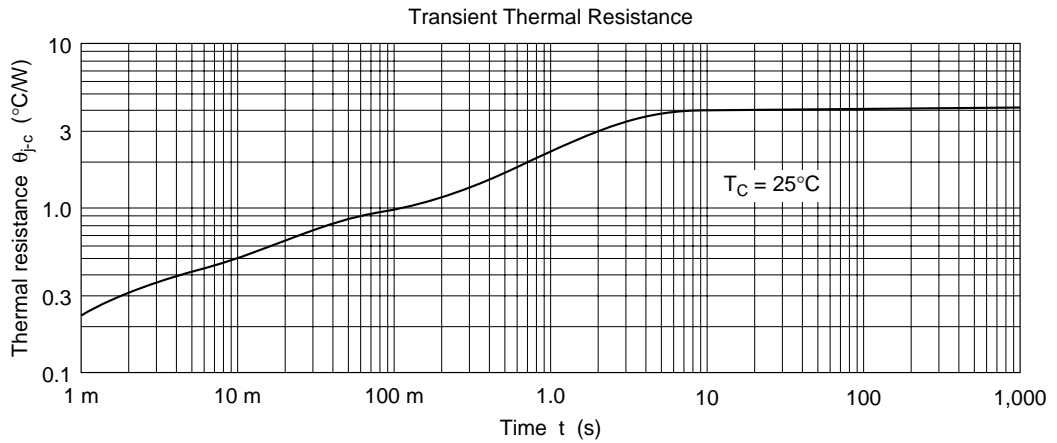
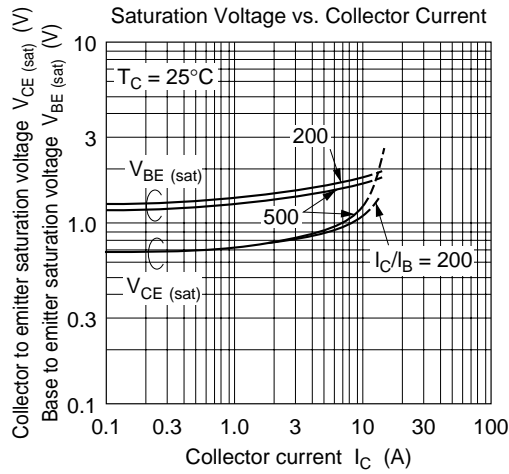
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

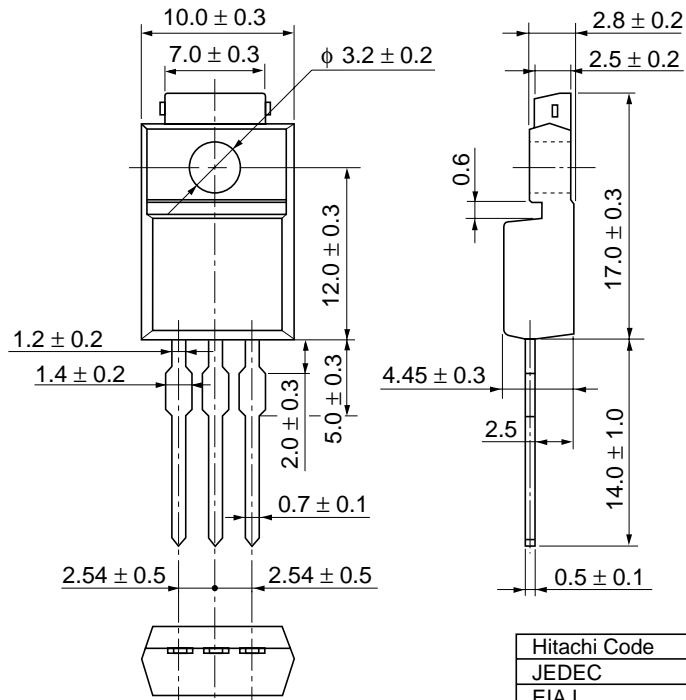
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	200	—	—	V	$I_C = 0.1 \text{ mA}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	200	—	—	V	$I_C = 25 \text{ mA}$, $R_{BE} = \infty$
Collector to emitter sustain voltage	$V_{CEO(SUS)}$	170	—	—	V	$I_C = 5 \text{ A}$, $L = 5 \text{ mH}$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 180 \text{ V}$, $I_E = 0$
	I_{CEO}	—	—	50		$V_{CE} = 180 \text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1500	—	—		$V_{CE} = 3 \text{ V}$, $I_C = 5 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	1.5	V	$I_C = 5 \text{ A}$, $I_B = 10 \text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	3.0		$I_C = 10 \text{ A}$, $I_B = 100 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2.0	V	$I_C = 5 \text{ A}$, $I_B = 10 \text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	3.5		$I_C = 10 \text{ A}$, $I_B = 100 \text{ mA}^{*1}$

Note: 1. Pulse test.





Unit: mm



Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.8 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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